

isc Silicon NPN Power Transistor

2SD1163A

DESCRIPTION

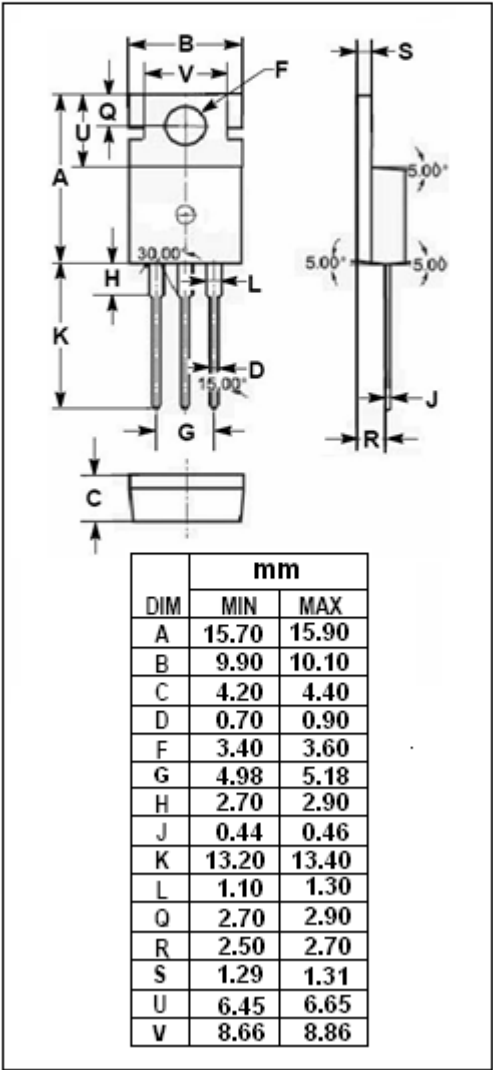
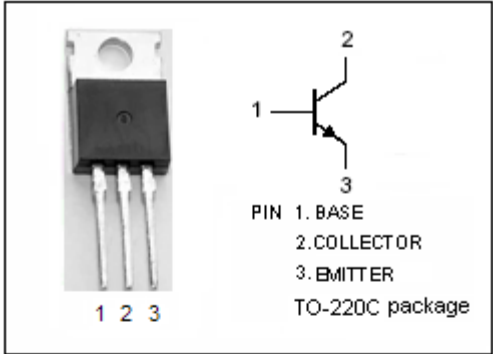
- Collector Current: $I_C = 7A$
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 150V(\text{Min.})$

APPLICATIONS

- Designed for TV horizontal deflection applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	350	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	7	A
I_{CM}	Collector Current-Peak	10	A
$I_{C(\text{surge})}$	Collector Current-Surge	20	A
P_C	Total Power Dissipation @ $T_C=25^\circ\text{C}$	40	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SD1163A****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA ; R _{BE} = ∞	150			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 10mA ; I _C = 0	6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 0.5A			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 0.5A			1.2	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 350V ; I _E = 0			5	mA
h _{FE}	DC Current Gain	I _C = 5A ; V _{CE} = 5V	25			
t _f	Fall Time	I _{CP} = 3.5A; I _{B1} = 0.45A			0.5	μ s